

NOT RECOMMENDED FOR NEW DESIGN USE DMG3402L



DMN3052L

N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

Low On-Resistance:

 $R_{DS(ON)} < 32m\Omega$ @ $V_{GS} = 10V$ $R_{DS(ON)} < 42m\Omega$ @ $V_{GS} = 4.5V$

 $R_{DS(ON)} < 64 \text{m}\Omega$ @ $V_{GS} = 2.5 \text{V}$

- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 2)
- "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

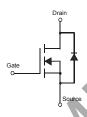
Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe.
 Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.008 grams (approximate)

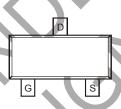
SOT-23







Equivalent Circuit



TOP VIEW

Maximum Ratings @TA = 25°C unless otherwise specified

Characteri	stic	Symbol	Value	Unit
Drain Source Voltage		V _{DSS}	30	V
Gate-Source Voltage		V_{GSS}	±12	V
Drain Current (Note 1)	$T_A = 25^{\circ}\text{C}$ $T_A = 70^{\circ}\text{C}$	I _D	5.4 4.6	А
Drain Current (Note 1)	Pulsed	I _{DM}	19	Α
Body-Diode Continuous Current (Note	: 1)	ls	2.0	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 1)	P_{D}	1.4	W
Thermal Resistance, Junction to Ambient @T _A = 25°C (Note 1)	$R_{ hetaJA}$	90	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

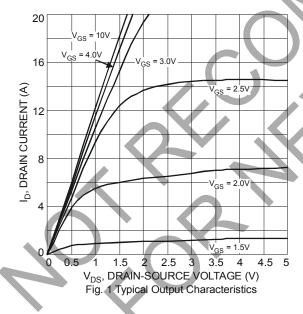
- 1. Device mounted on FR-4 PCB. t ≤5 sec.
- 2. No purposefully added lead.
- 3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

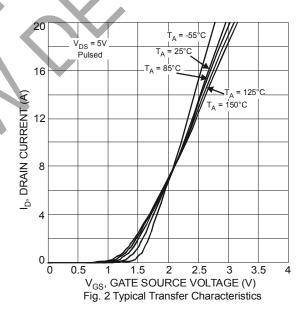


Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	_	V	$V_{GS} = 0V$, $I_D = 250 \mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μА	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Body Leakage	I _{GSS}		_	±80 ±800	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$ $V_{GS} = \pm 19V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 4)						
Gate Threshold Voltage	V _{GS(th)}	0.62	0.9	1.2	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
	R _{DS (ON)}	_	26	32	mΩ	$V_{GS} = 10V, I_D = 5.8A$
Static Drain-Source On-Resistance		_	33	42		$V_{GS} = 4.5V, I_D = 5.0A$
Otatic Brain-Oddice On-Resistance		_	52	64		$V_{GS} = 2.5V, I_D = 3.8A$
		_	78	100		$V_{GS} = 2.0V, I_D = 2.0A$
Forward Transconductance	Y _{fs}	_	8		S	$V_{DS} = 5V, I_{D} = 3.1A$
Source-Drain Diode Forward Voltage	V_{SD}		0.75	1.2	V	$V_{GS} = 0V, I_{S} = 2.0A$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	_	555	*	pF	TV 51/1/ 01/
Output Capacitance	Coss	-/	109	_	pF	$V_{DS} = 5V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	#	82	_ /	pF	11 - 1.0IVITZ
Total Gate Charge	Qg		6.3	-		V - 4 5 V V - 45 V
Gate-Source Charge	Q _{gs}	11-1	1.3		nC	$V_{GS} = 4.5V, V_{DS} = 15V,$ $I_{D} = 5.8A$
Gate-Drain Charge	Q_{gd}	1-1	1.7			ID - 3.0A

Notes: 4. Short duration pulse test used to minimize self-heating effect.

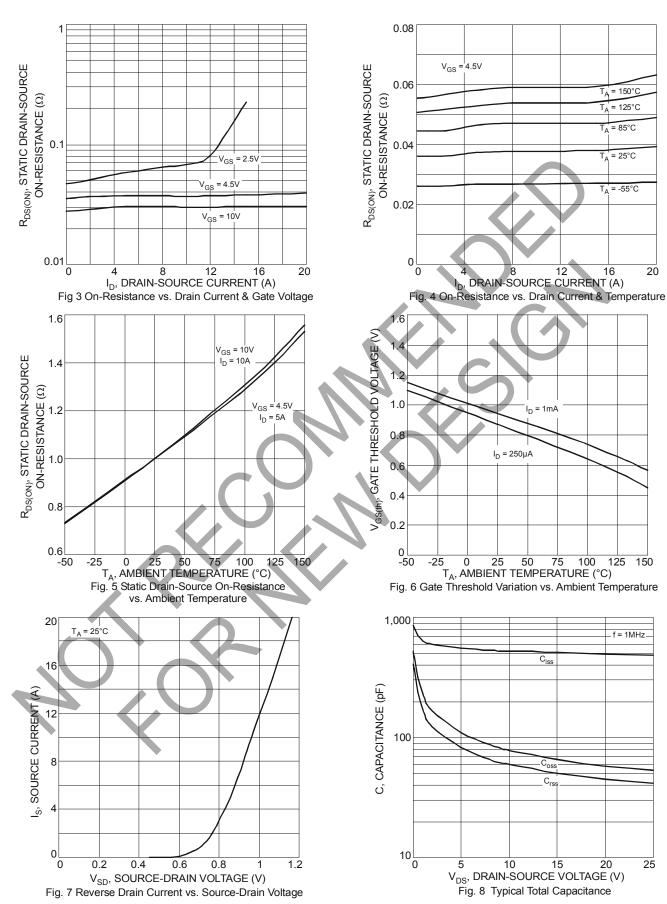




= 85°C

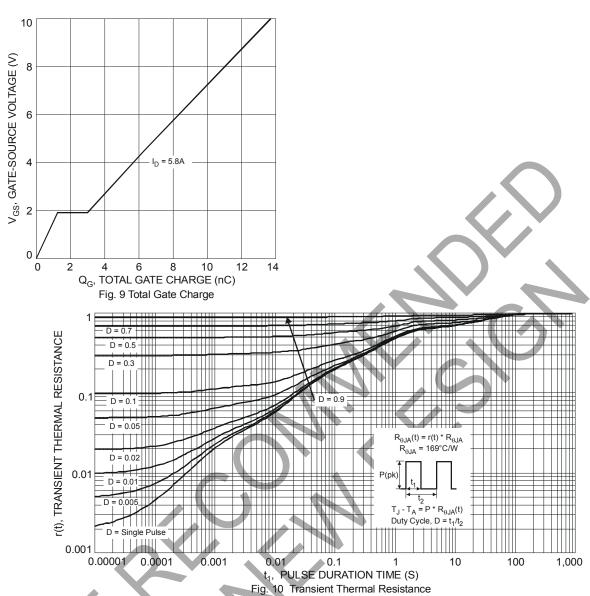
= 25°C





25



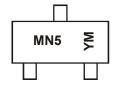


Ordering Information (Note 5)

Part Number	Case	Packaging
DMN3052L-7	SOT-23	3000/Tape & Reel

5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



MN5 = Product Type Marking Code YM = Date Code Marking

Y = Year (ex: V = 2008)

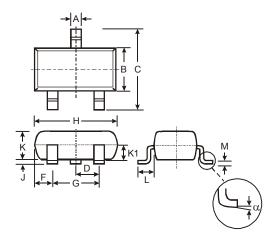
M = Month (ex: 9 = September)

Date Code Kev

Year	2008		2009	2010		2011	2012		2013	2014		2015
Code	V		W	X		Υ	Z		Α	В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	g Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

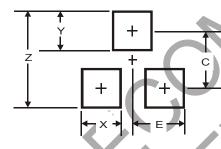


Package Outline Dimensions



	SOT-23						
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.903	1.10	1.00				
K1	-	- (0.400				
L	0.45	0.61	0.55				
M	0.085	0.18	0.11				
α	0°	8°	-				
All	All Dimensions in mm						

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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